

ANALOG Switch

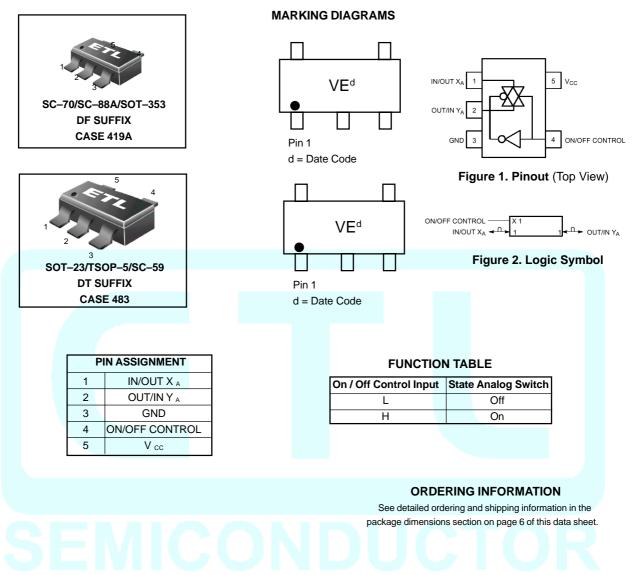
MC74VHC1GT66

The MC74VHC1GT66 is an advanced high speed CMOS bilateral analog switch fabricated with silicon gate CMOS technology. It achieves high speed propagation delays and low ON resistances while maintaining low power dissipation. This bilateral switch controls analog and digital voltages that may vary across the full power–supply range (from VCC to GND).

The MC74VHC1GT66 is compatible in function to a single gate of the very High Speed CMOS MC74VHCT4066. The device has been designed so that the ON resistances (RON) are much lower and more linear over input voltage.

The ON/OFF Control input is compatible with TTL-type input thresholds allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS logic or from 1.8 V CMOS logic to 3.0 V CMOS logic while operating at the high-voltage power supply. The input protection circuitry on this device allows overvoltage tolerance on the input, which provides protection when voltages of up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1GT66 to be used to interface 5 V circuits to 3 V circuits.

- High Speed: t $_{\text{PD}}$ = 20 ns (Typ) at V $_{\text{CC}}$ = 5 V
- Low Power Dissipation: I $_{\text{CC}}$ = 2 μA (Max) at T $_{\text{A}}$ = 25°C
- Diode Protection Provided on Inputs and Outputs
- Improved Linearity and Lower ON Resistance over Input Voltage
- On/Off Control Input Has OVT





MAXIMUM RATINGS

Symbol	Par	ameter	Value	Unit
V _{cc}	DC Supply Voltage		- 0.5 to + 7.0	V
V IN	DC Input Voltage		- 0.5 to +7.0	V
V IS	Analog Output Voltage		-0.5 to +7.0	V
l _{ік}	Input Diode Current		-20	mA
I _{cc}	DC Supply Current, V cc ar	id GND	+25	mA
Ρ _D	Power dissipation in still air	SC-88A (Note 2.)	200	mW
		TSOP5 (Note 2.)	450	
ΤL	Lead Temperature, 1 mm f	rom Case for 10 s	260	°C
T stg	Storage temperature		-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 3)	>2000	V
		Machine Model (Note 4)	> 200	
		Charged Device Model (Note 5)	N/A	
LATCH-UP	Latch–Up Performance	Above V _{cc} and Below GND at 125°C (Note 6)	± 500	mA

1. Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions eyond those indicated may adversely affect device reliability. Functional operation under absolute–maximum–rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

2. Derating – SC–88A Package: –3 mW/°C from 65°C to 125°C

- TSOP5 Package: -6 mW/°C from 65°C to 125°C

3. Tested to EIA/JESD22-A114-A

4. Tested to EIA/JESD22-A115-A

5. Tested to JESD22–C101–A

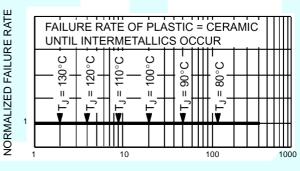
6. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit		
V _{cc}	DC Supply Voltage		2.0	5.5	V	
V _{IN}	DC Input Voltage		GND	5.5	V	
V _{IS}	Analog Input Voltage		GND	V cc	V	
TA	Operating Temperature Range		- 55	+ 125	°C	
t _r ,t _f	Input Rise and Fall Time	$V_{cc} = 3.3 \pm 0.3 V$	0	100	ns/V	
		$V_{cc} = 5.0 \pm 0.5 V$	0	20		

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS										
TIME TO 0.1% BOND FAILURES										
Junction	Junction Time, Time,									
Temperature °C	Hours	Years								
80	1,032,200	117.8								
90	419,300	47.9								
100	178,700	20.4								
110	79,600	9.4								
120	120 37,000 4.2									
130	17,800	2.0								
140	8,900	1.0								



TIME, YEARS

Figure 3. Failure Rate vs. Time Junction Temperature



DC ELECTRICAL CHARACTERISTICS

			V _{cc}	T _A = 25°C		$T_A \leq$	85 °C	T _A ≤	125°C		
Symbol	Parameter	Test Conditions	(V)	Min	Мах	Min	Max	Min	Max	Unit	
V IH	Minimum High–Level	R _{on} =Per Spec								V	
	Input Voltage		3.0	1.2		1.2		1.2			
	On/Off Control Input		4.5	2.0		2.0		2.0			
			5.5	2.0		2.0		2.0			
V IL	Maximum Low-Level	R _{on} =Per Spec								V	
	Input Voltage		3.0		0.53		0.53		0.53		
			4.5		0.8		0.8		0.8		
			5.5		0.8		0.8		0.8		
I _{IN}	Maximum Input	V IN =x Vcc or GND	0 to 5.5		±0.1		±1.0		±1.0	μA	
	Leakage Current										
	On/Off Control Input										
I cc	Maximum Quiescent	$V_{IN} = V_{CC} \text{ or } GND$	5.5		2.0		20		40	μA	
	Supply Current										
I _{CCT}	Quiescent Supply	On/Off Control	5.5		1.35		1.50		1.65	mA	
	Current	at 3.4 V									
R on	Maximum "ON"	V IN = V IH	3.0		60		70		100	Ω	
	Resistance	V IS = V CC or GND	4.5		45		50		60		
		I IS ≤10 mA (Figure 4.)	5.5		40		45		55		
I _{OFF}	Maximum Off–Channel	V IN = V IL	5.5		0.1		0.5		1.0	mA	
	Leakage Current	V IS = V CC or GND									
		Switch Off (Figure 5.)									

AC ELECTRICAL CHARACTERISTICS C $_{\text{load}}$ = 50 pF, Input t $_{\text{r}}/$ t $_{\text{f}}$ = 3.0 ns

			V cc	T _A = 25 °C		Τ₄<	85 °C	-55°C<	Г _А ≤125°C		
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
t PLH ,	Maximum Propogation	Y A = Open	2.0		1	5		6		7	ns
t PHL	Delay,	(Figure 14.)	3.0		0	2		3		4	
	Input X to Y		4.5		0	1		1		2	
			5.5		0	1		1		1	
t PLZ,	Maximum Propogation	R L = 1000 Ω	2.0		32	40		45		50	ns
t PHZ	Delay,	(Figure 15.)	3.0		28	35		40		45	
	ON/OFF Control to		4.5		24	30		35		40	
	Analog Output		5.5		20	25		30		35	
t PZL ,	Maximum Propogation	R L = 1000 Ω	2.0		32	40		45		50	ns
t PZH	Delay,	(Figure 15.)	3.0		28	35		40		45	
	ON/OFF Control to		4.5		24	30		35		40	
	Analog Output		5.5		20	25		30		35	
C IN	Maximum Input	ON/OFF Control Input	0.0		3	10		10		10	pF
	Capacitance	Contol Input = GND	5.0								
		Analog I/O			4	10		10		10	
		Feedthrough			4	10		10		10	
				Туріс	al @ 2	2 5°C, V	cc = 5.0	V			
C PD	Power Dissipation Capacitance (Note 6)					18					pF

7. C _{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \bullet C_{PD}$ is used to determine the no–load dynamic power consumption; $P_{D} = C_{PD} \bullet V_{CC}^{2} \bullet f_{in} + I_{CC} \bullet V_{CC}$.



ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

Symbol	Parameter	Test Conditions	V _{cc}	Limit 25°C	Unit
BW	Maximum On-Channel Bandwidth	f in = 1 MHz Sine Wave	3.0	150	MHz
	or Minimum Frequency Response	Adjust f in voltage to obtain 0 dBm at V OS	4.5	175	
	(Figure 10.)	Increase f in = frequency until dB meter reads -3 dB	5.5	180	
		R L = 50 Ω , C L = 10 pF			
ISO off	Off–Channel Feedthrough	f in = Sine Wave	3.0	-80	dB
	Isolation	Adjust f in voltage to obtain 0 dBm at V IS	4.5	-80	
	(Figure 11.)	f in = 10 kHz, R L = 600 Ω , C L = 50 pF	5.5	-80	
NOISE feed	Feedthrough Noise Control to	V in \leq 1 MHz Square Wave (t r = t f = 2ns)	3.0	45	тVрр
	Switch	Adjust R \perp at setup so that I s = 0 A	4.5	60	
	(Figure 12.)	R L = 600 Ω , C L = 50 pF	5.5	130	
THD	Total Harmonic Distortion	f in = 1 kHz, R L = 10 k Ω , C L = 50 pF			%
	(Figure 13.)	THD = THD Measured – THD Source			
		V IS = 3.0 V PP sine wave	3.3	0.30	
		V IS = 5.0 V PP sine wave	5.5	0.15	

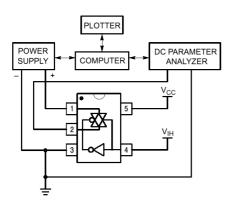
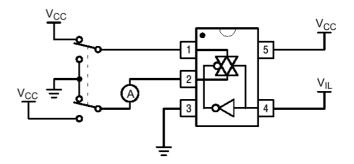
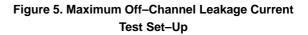
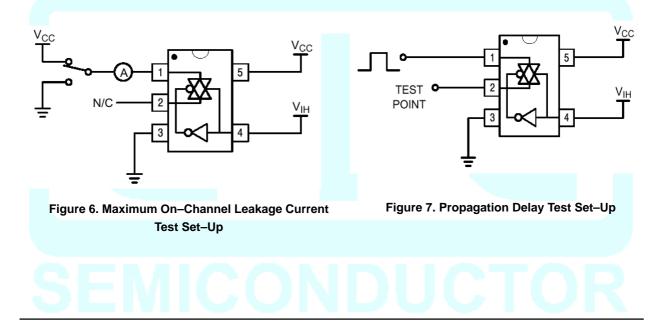


Figure 4. On Resistance Test Set–Up

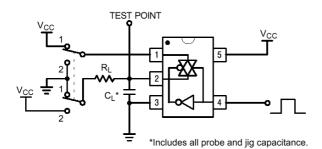


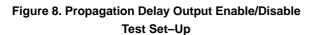


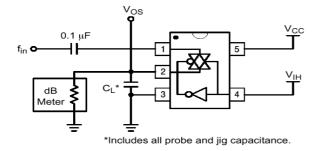


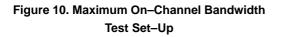


Switch to Position 1 when testing t $_{\rm PLZ}$ and t $_{\rm PZL}$ Switch to Position 2 when testing t $_{\rm PHZ}$ and t $_{\rm PZH}$









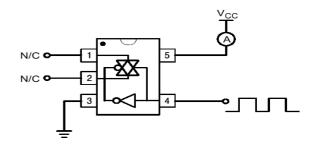


Figure 9. Power Dissipation Capacitance Test Set–Up

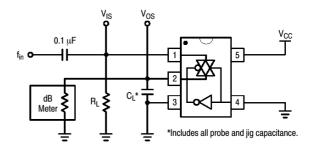
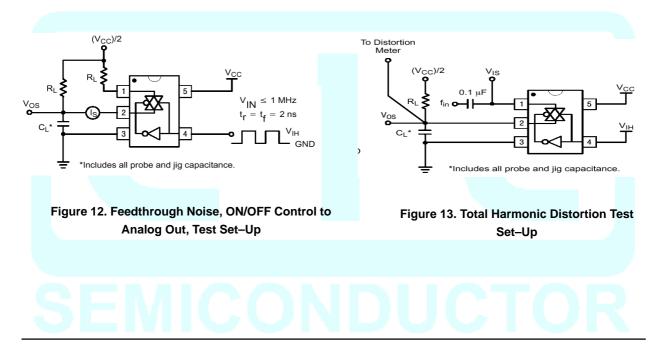


Figure 11. Off–Channel Feedthrough Isolation Test Set–Up





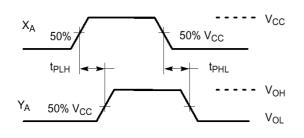


Figure 14. Propagation Delay, Analog In to Analog Out Waveforms

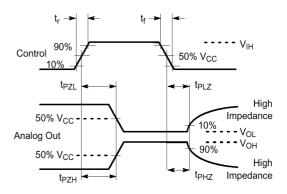


Figure 15. Propagation Delay, ON/OFF Control

DEVICE ORDERING INFORMATION

Device			Device	Nomenclat	ure		Package Type Tape and	Tapo and
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	(Name/SOT#/ Common Name)	Reel Size
MC74VHC1GT66DFT	MC	74	VHC1G	T66	DF	T1	SC-70/SC-88A/	178 mm (7 in)
							SOT-353	3000 Unit
MC74VHC1GT66DFT2	2 MC	74	VHC1G	T66	DF	T2	SC-70/SC-88A/	178 mm (7 in)
							SOT-353	3000 Unit
MC74VHC1GT66DFT4	4 MC	74	VHC1G	T66	DF	T4	SC-70/SC-88A/	330 mm (13 in)
							SOT-353	10,000 Unit
MC74VHC1GT66DTT	MC	74	VHC1G	T66	DT	T1	SOT-23/TSOPS/	178 mm (7 in)
							SC-59	3000 Unit
MC74VHC1GT66DTT	3 MC	74	VHC1G	T66	DT	Т3	SOT-23/TSOPS/	330 mm (13 in)
							SC-59	10,000 Unit

